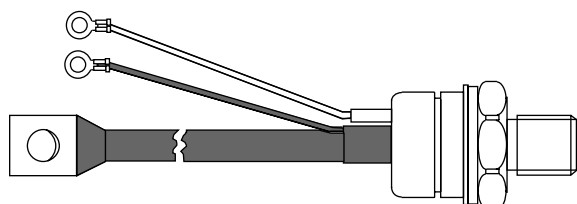


Phase Control Thyristors (Stud Version), 200 A


TO-209AB (TO-93)

FEATURES

- Center amplifying gate
- International standard case TO-209AB (TO-93)
- Hermetic metal case with ceramic insulator
(Also available with glass-metal seal up to 1200 V)
- Compression bonded encapsulation for heavy duty operations such as severe thermal cycling
- Lead (Pb)-free
- Designed and qualified for industrial level


RoHS
COMPLIANT

PRODUCT SUMMARY

$I_{T(AV)}$	200 A
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TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS

PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$		200	A
	T_C	85	°C
$I_{T(RMS)}$		314	A
I_{TSM}	50 Hz	5000	A
	60 Hz	5230	
I^2t	50 Hz	125	kA ² s
	60 Hz	114	
V_{DRM}/V_{RRM}		400 to 2000	V
t_q	Typical	100	μs
T_J		- 40 to 125	°C

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS

TYPE NUMBER	VOLTAGE CODE	V_{DRM}/V_{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA
ST180S	04	400	500	30
	08	800	900	
	12	1200	1300	
	16	1600	1700	
	20	2000	2100	

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current at case temperature	I _{T(AV)}	180° conduction, half sine wave			200	A
					85	°C
Maximum RMS on-state current	I _{T(RMS)}	DC at 76 °C case temperature			314	A
Maximum peak, one-cycle non-repetitive surge current	I _{TSM}	t = 10 ms	No voltage reapplied	Sinusoidal half wave, initial T _J = T _J maximum	5000	
		t = 8.3 ms			5230	
		t = 10 ms	100 % V _{RRM} reapplied		4200	
		t = 8.3 ms			4400	
Maximum I ² t for fusing	I ² t	t = 10 ms	No voltage reapplied		125	kA ² s
		t = 8.3 ms		114		
		t = 10 ms	100 % V _{RRM} reapplied	88		
		t = 8.3 ms		81		
Maximum I ² √t for fusing	I ² √t	t = 0.1 to 10 ms, no voltage reapplied			1250	kA ² /√s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % × π × I _{T(AV)}) < I < π × I _{T(AV)} , T _J = T _J maximum			1.08	V
High level value of threshold voltage	V _{T(TO)2}	(I > π × I _{T(AV)}), T _J = T _J maximum			1.14	
Low level value of on-state slope resistance	r _{t1}	(16.7 % × π × I _{T(AV)}) < I < π × I _{T(AV)} , T _J = T _J maximum			1.18	mΩ
High level value of on-state slope resistance	r _{t2}	(I > π × I _{T(AV)}), T _J = T _J maximum			1.14	
Maximum on-state voltage	V _{TM}	I _{pk} = 570 A, T _J = 125 °C, t _p = 10 ms sine pulse			1.75	V
Maximum holding current	I _H	T _J = T _J maximum, anode supply 12 V resistive load			600	mA
Maximum (typical) latching current	I _L				1000 (300)	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	di/dt	Gate drive 20 V, 20 Ω, $t_r \leq 1 \text{ μs}$ $T_J = T_J \text{ maximum}$, anode voltage $\leq 80 \% V_{DRM}$	1000	A/μs
Typical delay time	t_d	Gate current 1 A, $di_g/dt = 1 \text{ A/μs}$ $V_d = 0.67 \% V_{DRM}$, $T_J = 25 \text{ °C}$	1.0	μs
Typical turn-off time	t_q	$I_{TM} = 300 \text{ A}$, $T_J = T_J \text{ maximum}$, $di/dt = 20 \text{ A/μs}$, $V_R = 50 \text{ V}$, $dV/dt = 20 \text{ V/μs}$, gate 0 V 100 Ω, $t_p = 500 \text{ μs}$	100	

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ maximum}$ linear to 80 % rated V_{DRM}	500	V/μs
Maximum peak reverse and off-state leakage current	I_{RRM} , I_{DRM}	$T_J = T_J \text{ maximum}$, rated V_{DRM}/V_{RRM} applied	30	mA



TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES		UNITS
				TYP.	MAX.	
Maximum peak gate power	P _{GM}	T _J = T _J maximum, t _p ≤ 5 ms		10		W
Maximum average gate power	P _{G(AV)}	T _J = T _J maximum, f = 50 Hz, d% = 50		2.0		
Maximum peak positive gate current	I _{GM}	T _J = T _J maximum, t _p ≤ 5 ms		3.0		A
Maximum peak positive gate voltage	+ V _{GM}	T _J = T _J maximum, t _p ≤ 5 ms		20		V
Maximum peak negative gate voltage	- V _{GM}			5.0		
DC gate current required to trigger	I _{GT}	T _J = - 40 °C	Maximum required gate trigger/ current/voltage are the lowest value which will trigger all units 12 V anode to cathode applied	180	-	mA
		T _J = 25 °C		90	150	
		T _J = 125 °C		40	-	
DC gate voltage required to trigger	V _{GT}	T _J = - 40 °C		2.9	-	V
		T _J = 25 °C		1.8	3.0	
		T _J = 125 °C		1.2	-	
DC gate current not to trigger	I _{GD}	T _J = T _J maximum	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V _{DRM} anode to cathode applied	10		mA
DC gate voltage not to trigger	V _{GD}			0.25		V

THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum operating junction temperature range	T_J		- 40 to 125	°C
Maximum storage temperature range	T_{Stg}		- 40 to 150	
Maximum thermal resistance, junction to case	R_{thJC}	DC operation	0.105	K/W
Maximum thermal resistance, case to heatsink	R_{thC-hs}	Mounting surface, smooth, flat and greased	0.04	
Mounting torque, ± 10 %		Non-lubricated threads	31 (275)	N · m (lbf · in)
		Lubricated threads	24.5 (210)	
Approximate weight			280	g
Case style		See dimensions - link at the end of datasheet	TO-209AB (TO-93)	

ΔR_{thJC} CONDUCTION				
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.015	0.012	$T_J = T_J$ maximum	K/W
120°	0.019	0.020		
90°	0.025	0.027		
60°	0.036	0.037		
30°	0.060	0.060		

Note

- The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

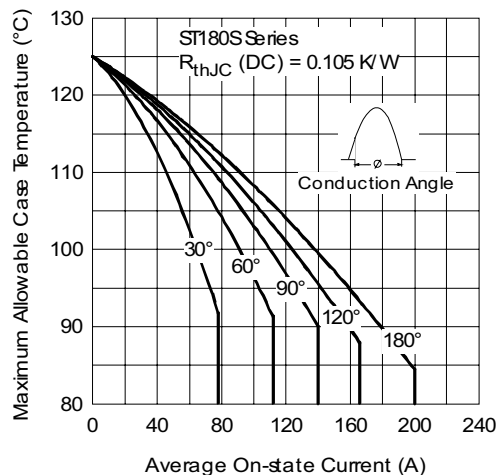


Fig. 1 - Current Ratings Characteristics

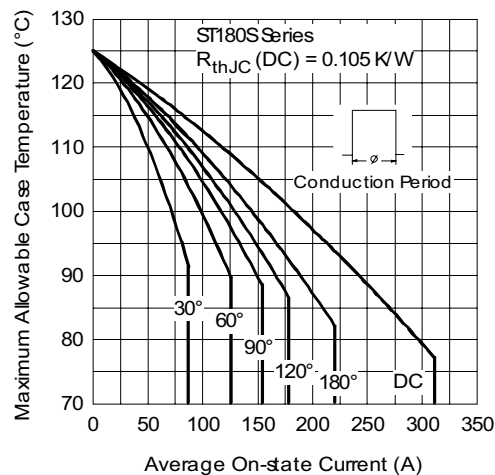


Fig. 2 - Current Ratings Characteristics

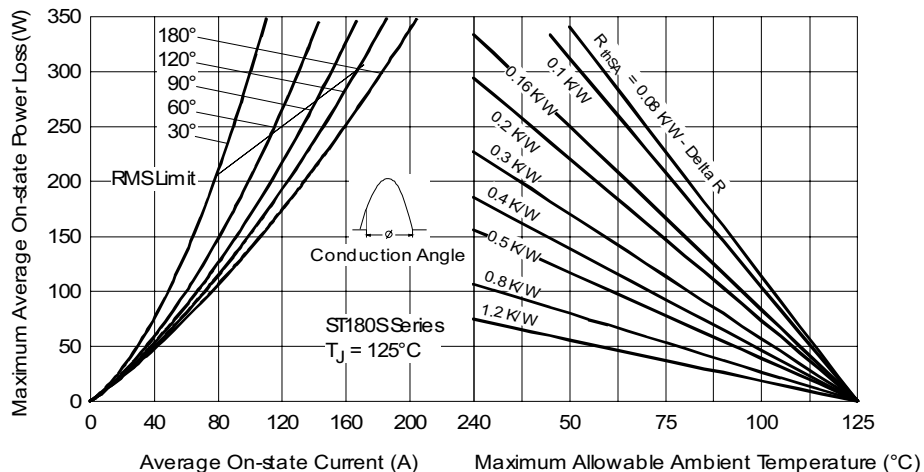


Fig. 3 - On-State Power Loss Characteristics

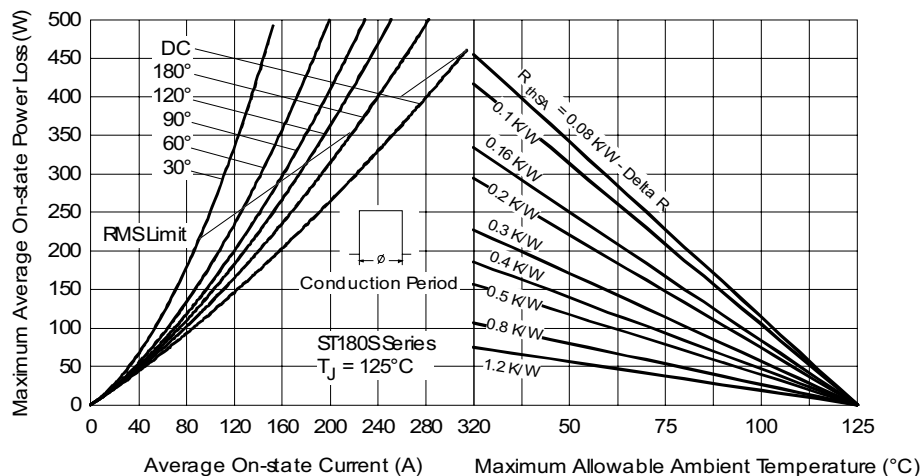


Fig. 4 - On-State Power Loss Characteristics

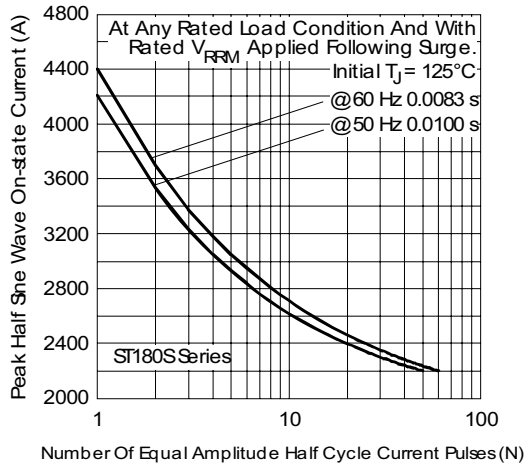


Fig. 5 - Maximum Non-Repetitive Surge Current

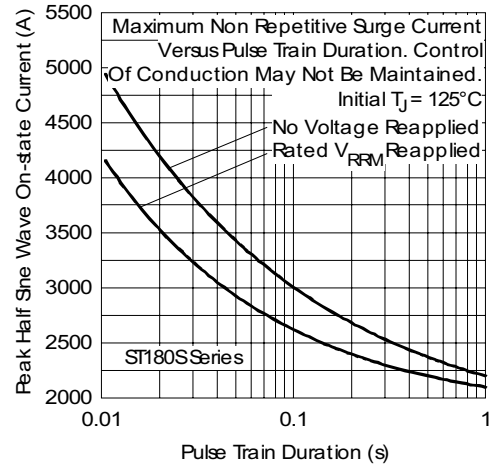


Fig. 6 - Maximum Non-Repetitive Surge Current

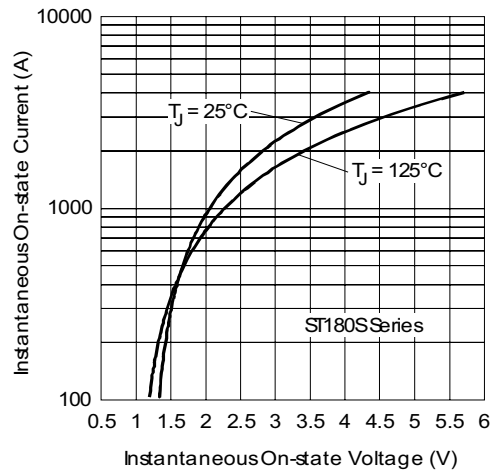


Fig. 7 - On-State Voltage Drop Characteristics

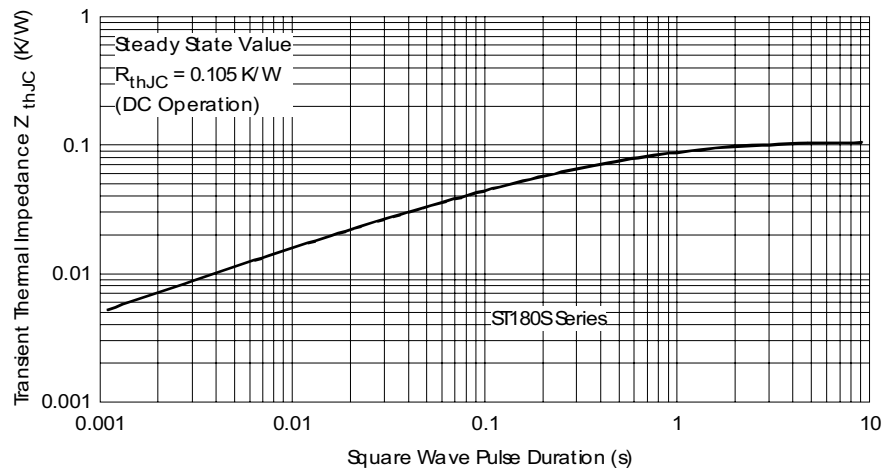


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

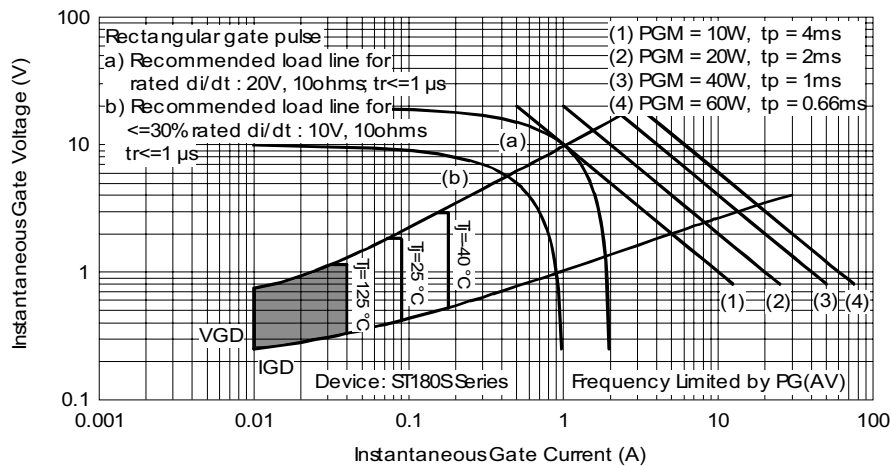


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	ST	18	0	S	20	P	0	-	PbF
	1	2	3	4	5	6	7	8	9
1	- Thyristor								
2	- Essential part number								
3	- 0 = Converter grade								
4	- S = Compression bonding stud								
5	- Voltage code x 100 = V_{RRM} (see Voltage Ratings table)								
6	- P = Stud base 3/4"-16UNF2A threads								
7	- 0 = Eyelet terminals (gate and auxiliary cathode leads) 1 = Fast-on terminals (gate and auxiliary cathode leads)								
8	- V = Glass-metal seal (only up to 1200 V) None = Ceramic housing (over 1200 V)								
9	- Lead (Pb)-free								

Note: For metric device M16 x 1.5 contact factory

LINKS TO RELATED DOCUMENTS	
Dimensions	http://www.vishay.com/doc?95082



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